

In the Claims:

1. (currently amended) A substrate including a scatterometry target and other features each having at least one of a microelectronic function or a microelectromechanical function, said scatterometry target comprising:

a plurality of parallel elongated features extending in a first direction of said scatterometry target, each of said features having a width in a widthwise direction transverse to said ~~length in a lengthwise first direction~~, wherein a ratio of a length of said scatterometry target in said first direction to said width of each feature is greater than or equal to about 50, said width of said elongated features mimicking a width of said other features; and

a plurality of stress-relief features disposed at a plurality of positions along said ~~length of each said elongated feature~~.

2. (currently amended) The ~~scatterometry target-substrate of claim 1 wherein said elongated features include linearly extending features~~, wherein said stress-relief features include connecting features which connect pairs of said elongated ~~linearly extending features in a direction transverse to said lengthwise direction~~.

3. (currently amended) The substrate scatterometry target of claim 1 wherein said stress-relief features include gaps, said gaps interrupting said elongated features at intervals along said length of said scatterometry target.

4. (currently amended) The substrate ~~scatterometry target~~ of claim 2 wherein said stress-relief features further include gaps, said gaps interrupting said elongated features, wherein said scatterometry target including said connecting features and said gaps is adapted to produce a return signal mimicking a return signal from a scatterometry target not having said stress-relief features.

5. (currently amended) The ~~scatterometry target~~ substrate of claim 4 wherein said elongated ~~linearly extending~~ features are provided in a layer of photoresist.

6. (currently amended) The substrate ~~scatterometry target~~ of claim 5 wherein said elongated ~~linearly extending~~ features mimic patterned photoresist layer features at critical dimension.

7. (currently amended) The substrate ~~scatterometry target~~ of claim 1 wherein said stress-relief features include jogs in said ~~parallel~~ elongated features.

8. (currently amended) The ~~scatterometry target~~ substrate of claim 2 wherein said connecting features include bridges, said bridges satisfying the relation $2\% - 0.02 > (N_B L_B) / NL$, where N_B is the number of bridges of the a grating, L_B the length of each bridge, N the number of lines of the grating, and L the length of the grating.

9. (currently amended) The substrate ~~scatterometry target~~ of claim 2 wherein said connecting features include bridges, said bridges satisfying the relation $2\% - 0.02 >$

$(N_G L_G)/NL$, where N_G is the number of gaps of ~~the~~ a grating, L_G the length of each gap, N the number of lines of the grating, and L the length of the grating.

10. (currently amended) The ~~scatterometry target~~ substrate of claim 7 wherein said jogs satisfy the relation $f_J(N_J/N)(W/L) < 2\%0.02$, where N_J is the number of jogs of ~~the~~ a grating, N the number of lines of the grating, L the length of the grating, W the width of the grating, and f_J a process factor.

11. (currently amended) A substrate including a scatterometry target and other features each having at least one of a microelectronic function or a microelectromechanical function, said scatterometry target comprising:

a plurality of parallel elongated features extending in a first direction of said scatterometry target, each of said features having a width in a widthwise direction transverse to said length in a lengthwise first direction, each said elongated feature having jogs disposed at a plurality of locations along said length, said jogs causing said scatterometry target to produce a return signal which is sensitive to photolithographic defocus, wherein a ratio of a length of said scatterometry target in said first direction to said width of each feature is greater than or equal to about 50, said width of said elongated features mimicking a width of said other features.

12. (currently amended) The ~~scatterometry target~~ substrate of claim 11 wherein said jogs satisfy the relation $f_J(N_J/N)(W/L) > 1$, where N_J is the number of jogs of ~~the~~ a

grating, N the number of lines of the grating, L the length of the grating, W the width of the grating, and f_j a process factor.

13-18. (cancelled)

19. (new) The substrate of claim 1, wherein said scatterometry target is adapted to produce a return signal mimicking a return signal from a scatterometry target not having said stress-relief features.